## 1. General description

PNP high-voltage low  $V_{CEsat}$  transistor in a SOT223 (SC-73) medium power Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8115Z

### 2. Features and benefits

- · High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub>
- Medium power SMD plastic package
- AEC-Q101 qualified

### 3. Applications

- · LED driver for LED chain module
- LCD backlighting
- · High Intensity Discharge (HID) front lighting
- · Automotive motor management
- · Hook switch for wired telecom
- Switch mode power supply

### 4. Quick reference data

Table 1. Quick reference data

| Symbol           | Parameter                 | Conditions                                            | Min | Тур | Max  | Unit |
|------------------|---------------------------|-------------------------------------------------------|-----|-----|------|------|
| V <sub>CEO</sub> | collector-emitter voltage | open base                                             | -   | -   | -150 | V    |
| Ic               | collector current         |                                                       | -   | -   | -1   | Α    |
| h <sub>FE</sub>  | DC current gain           | $V_{CE}$ = -10 V; $I_{C}$ = -50 mA; $T_{amb}$ = 25 °C | 100 | 220 | -    |      |

## 5. Pinning information

**Table 2. Pinning information** 

| auto 21. mmily mornidation |        |             |                    |                |  |  |  |
|----------------------------|--------|-------------|--------------------|----------------|--|--|--|
| Pin                        | Symbol | Description | Simplified outline | Graphic symbol |  |  |  |
| 1                          | В      | base        | 4                  | C              |  |  |  |
| 2                          | С      | collector   |                    | В              |  |  |  |
| 3                          | Е      | emitter     |                    |                |  |  |  |
| 4                          | С      | collector   | □1 □2 □3           | Ė              |  |  |  |
|                            |        |             | SC-73 (SOT223)     | sym028         |  |  |  |



### 150 V, 1 A PNP high-voltage low VCEsat transistor

# 6. Ordering information

#### **Table 3. Ordering information**

| Type number | Package |                                                                                                                 |         |  |  |  |
|-------------|---------|-----------------------------------------------------------------------------------------------------------------|---------|--|--|--|
|             | Name    | Description                                                                                                     | Version |  |  |  |
| PBHV9115Z   |         | plastic, surface-mounted package with increased heatsink; 4 leads; 2.3 mm pitch; 6.5 mm x 3.5 mm x 1.65 mm body | SOT223  |  |  |  |

## 7. Marking

#### Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PBHV9115Z   | V9115Z       |

# 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                 | Conditions                          |     | Min | Max  | Unit |
|------------------|---------------------------|-------------------------------------|-----|-----|------|------|
| V <sub>CBO</sub> | collector-base voltage    | open emitter                        |     | -   | -200 | V    |
| $V_{CEO}$        | collector-emitter voltage | open base                           |     | -   | -150 | V    |
| V <sub>EBO</sub> | emitter-base voltage      | open collector                      |     | -   | -6   | V    |
| I <sub>C</sub>   | collector current         |                                     |     | -   | -1   | А    |
| I <sub>CM</sub>  | peak collector current    | single pulse; t <sub>p</sub> ≤ 1 ms |     | -   | -2   | Α    |
| I <sub>BM</sub>  | peak base current         |                                     |     | -   | -400 | mA   |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | [1] | -   | 0.7  | W    |
|                  |                           |                                     | [2] | -   | 1.4  | W    |
| Tj               | junction temperature      |                                     |     | -   | 150  | °C   |
| T <sub>amb</sub> | ambient temperature       |                                     |     | -55 | 150  | °C   |
| T <sub>stg</sub> | storage temperature       |                                     |     | -65 | 150  | °C   |

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

PBHV9115Z

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

#### 150 V, 1 A PNP high-voltage low VCEsat transistor

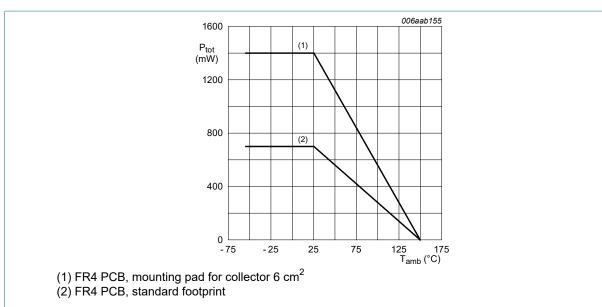


Fig. 1. Power derating curves

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol                | Parameter                                        | Conditions  |     | Min | Тур | Max | Unit |
|-----------------------|--------------------------------------------------|-------------|-----|-----|-----|-----|------|
| R <sub>th(j-a)</sub>  | thermal resistance from                          | in free air | [1] | -   | -   | 175 | K/W  |
| junction to ambient   |                                                  | [2]         | -   | -   | 89  | K/W |      |
| R <sub>th(j-sp)</sub> | thermal resistance from junction to solder point |             |     | -   | -   | 20  | K/W  |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

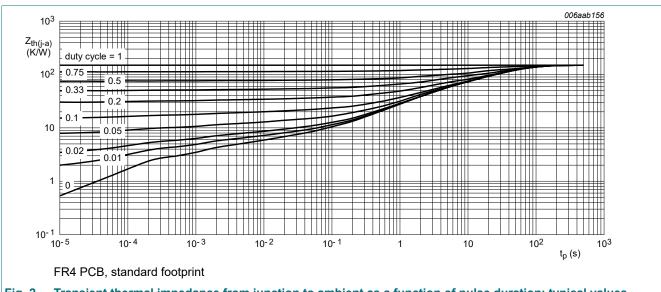
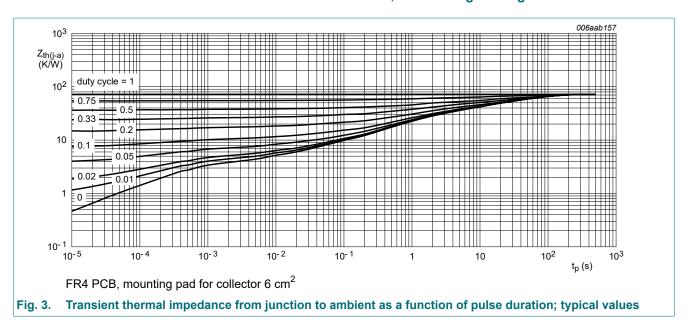


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

### 150 V, 1 A PNP high-voltage low VCEsat transistor



### 10. Characteristics

**Table 7. Characteristics** 

| Symbol             | Parameter                            | Conditions                                                                              | Min | Тур   | Max  | Unit |
|--------------------|--------------------------------------|-----------------------------------------------------------------------------------------|-----|-------|------|------|
| I <sub>CBO</sub>   | collector-base cut-off               | V <sub>CB</sub> = -120 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C                | -   | -     | -100 | nA   |
|                    | current                              | V <sub>CB</sub> = -120 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C                 | -   | -     | -10  | μA   |
| I <sub>EBO</sub>   | emitter-base cut-off current         | V <sub>EB</sub> = -4 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C                  | -   | -     | -100 | nA   |
| I <sub>CES</sub>   | collector-emitter cut-off current    | V <sub>CE</sub> = -120 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C               | -   | -     | -100 | nA   |
| h <sub>FE</sub>    | DC current gain                      | V <sub>CE</sub> = -10 V; I <sub>C</sub> = -50 mA; T <sub>amb</sub> = 25 °C              | 100 | 220   | -    |      |
|                    |                                      | $V_{CE}$ = -10 V; $I_{C}$ = -100 mA; $T_{amb}$ = 25 °C                                  | 100 | 220   | -    |      |
|                    |                                      | $V_{CE}$ = -10 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C | 10  | 30    | -    |      |
| V <sub>CEsat</sub> | collector-emitter saturation voltage | $I_C$ = -100 mA; $I_B$ = -10 mA; $T_{amb}$ = 25 °C                                      | -   | -60   | -120 | mV   |
|                    |                                      | I <sub>C</sub> = -100 mA; I <sub>B</sub> = -20 mA; T <sub>amb</sub> = 25 °C             | -   | -50   | -100 | mV   |
|                    |                                      | $I_C$ = 500 mA; $I_B$ = -100 mA;<br>$T_{amb}$ = 25 °C                                   | -   | -150  | -300 | mV   |
| V <sub>BEsat</sub> | base-emitter saturation voltage      | $I_C$ = -1 A; $I_B$ = -200 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C      | -   | -1.05 | -1.2 | V    |
| t <sub>d</sub>     | delay time                           | $V_{CC}$ = -6 V; $I_{C}$ = -0.5 A; $I_{Bon}$ = -0.1 A;                                  | -   | 8     | -    | ns   |
| t <sub>r</sub>     | rise time                            | I <sub>Boff</sub> = 0.1 A; T <sub>amb</sub> = 25 °C                                     | -   | 282   | -    | ns   |
| t <sub>on</sub>    | turn-on time                         |                                                                                         | -   | 290   | -    | ns   |
| t <sub>s</sub>     | storage time                         |                                                                                         | -   | 430   | -    | ns   |
| t <sub>f</sub>     | fall time                            |                                                                                         | -   | 300   | -    | ns   |
| t <sub>off</sub>   | turn-off time                        |                                                                                         | -   | 730   | -    | ns   |
| f <sub>T</sub>     | transition frequency                 | $V_{CE}$ = -10 V; $I_{C}$ = -10 mA; f = 100 MHz; $T_{amb}$ = 25 °C                      | -   | 115   | -    | MHz  |
| C <sub>c</sub>     | collector capacitance                | $V_{CB}$ = -20 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C          | -   | 10    | -    | pF   |
| C <sub>e</sub>     | emitter capacitance                  | $V_{EB}$ = -0.5 V; $I_{C}$ = 0 A; $i_{c}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C         | -   | 150   | -    | pF   |

### 150 V, 1 A PNP high-voltage low VCEsat transistor

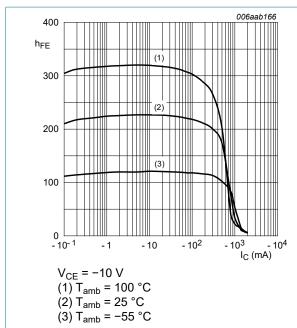


Fig. 4. DC current gain as a function of collector

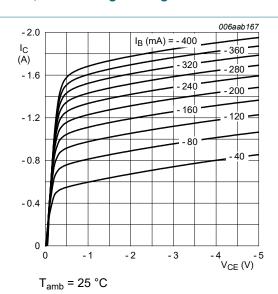


Fig. 5. Collector current as a function of collectoremitter voltage; typical values

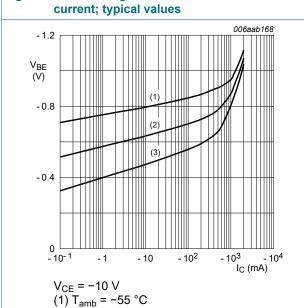
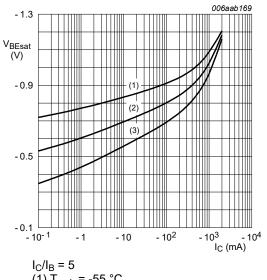


Fig. 6. Base-emitter voltage as a function of collector current; typical values

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3) T<sub>amb</sub> = 100 °C



(1)  $T_{amb} = -55$  °C (2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

### 150 V, 1 A PNP high-voltage low VCEsat transistor

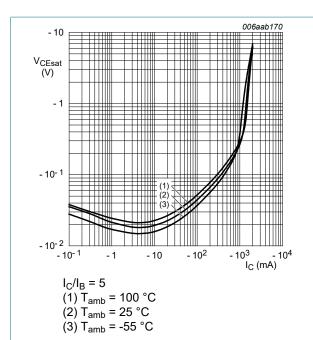


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

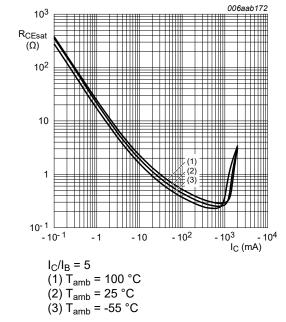


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

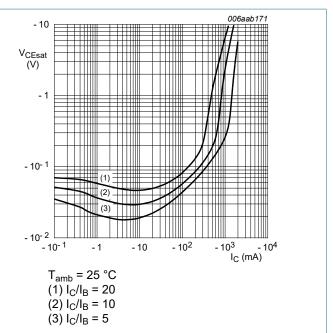


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

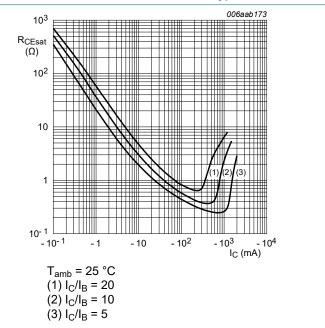
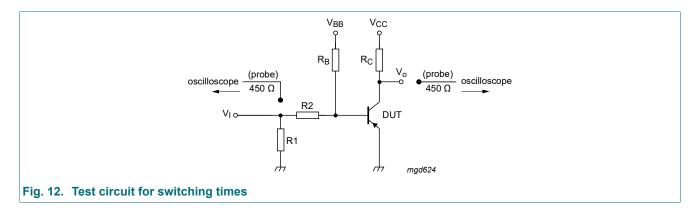


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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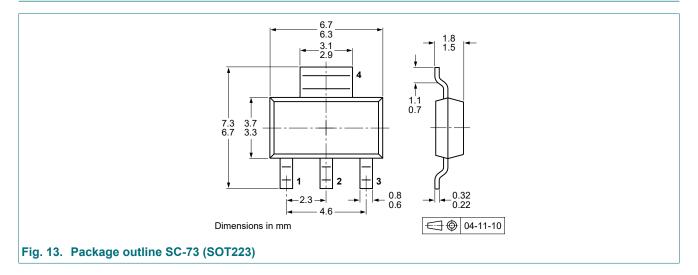
## 11. Test information



### **Quality information**

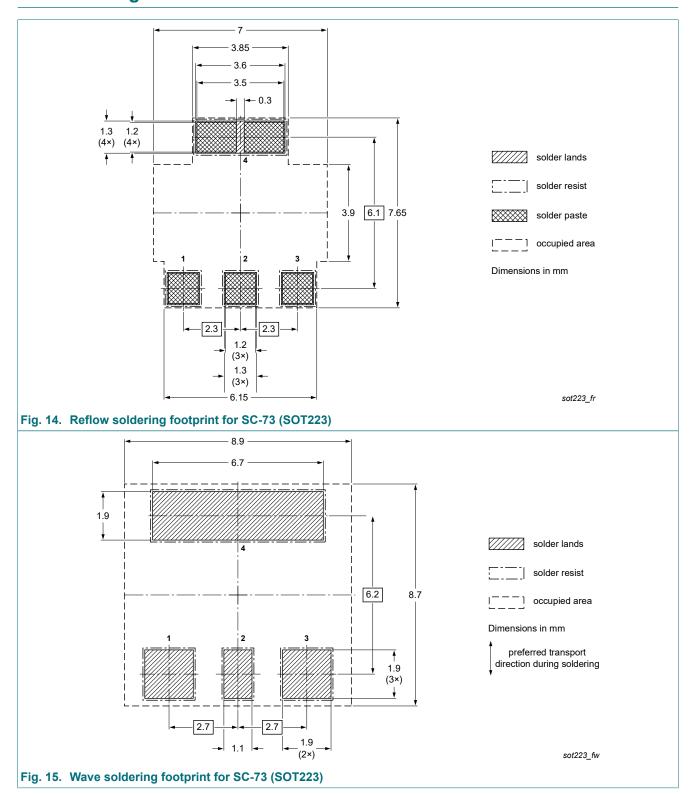
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 12. Package outline



### 150 V, 1 A PNP high-voltage low VCEsat transistor

# 13. Soldering



## 150 V, 1 A PNP high-voltage low VCEsat transistor

# 14. Revision history

#### **Table 8. Revision history**

| Data sheet ID  | Release date | Data sheet status                                                     | Change notice | Supersedes   |  |  |  |
|----------------|--------------|-----------------------------------------------------------------------|---------------|--------------|--|--|--|
| PBHV9115Z v.3  | 20230717     | Product data sheet                                                    | -             | PBHV9115Z _2 |  |  |  |
| Modifications: | Nexperia.    | nta sheet has been redesion adapted to the new concernation" removed. |               | , ,          |  |  |  |
| PBHV9115Z _2   | 20090109     | Product data sheet                                                    | -             | PBHV9115Z _1 |  |  |  |
| PBHV9115Z _1   | 20080214     | Product data sheet                                                    | -             | -            |  |  |  |

### 15. Legal information

#### **Data sheet status**

| Document status [1][2]         | Product<br>status [3] | Definition                                                                            |
|--------------------------------|-----------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development           | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification         | This document contains data from the preliminary specification.                       |
| Product [short]<br>data sheet  | Production            | This document contains the product specification.                                     |

- Please consult the most recently issued document before initiating or completing a design.
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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 17 July 2023

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